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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	516096
Number of I/O	221
Number of Gates	3000000
Voltage - Supply	1.14V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	324-BGA
Supplier Device Package	324-FBGA (19x19)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a3pe3000l-fg324

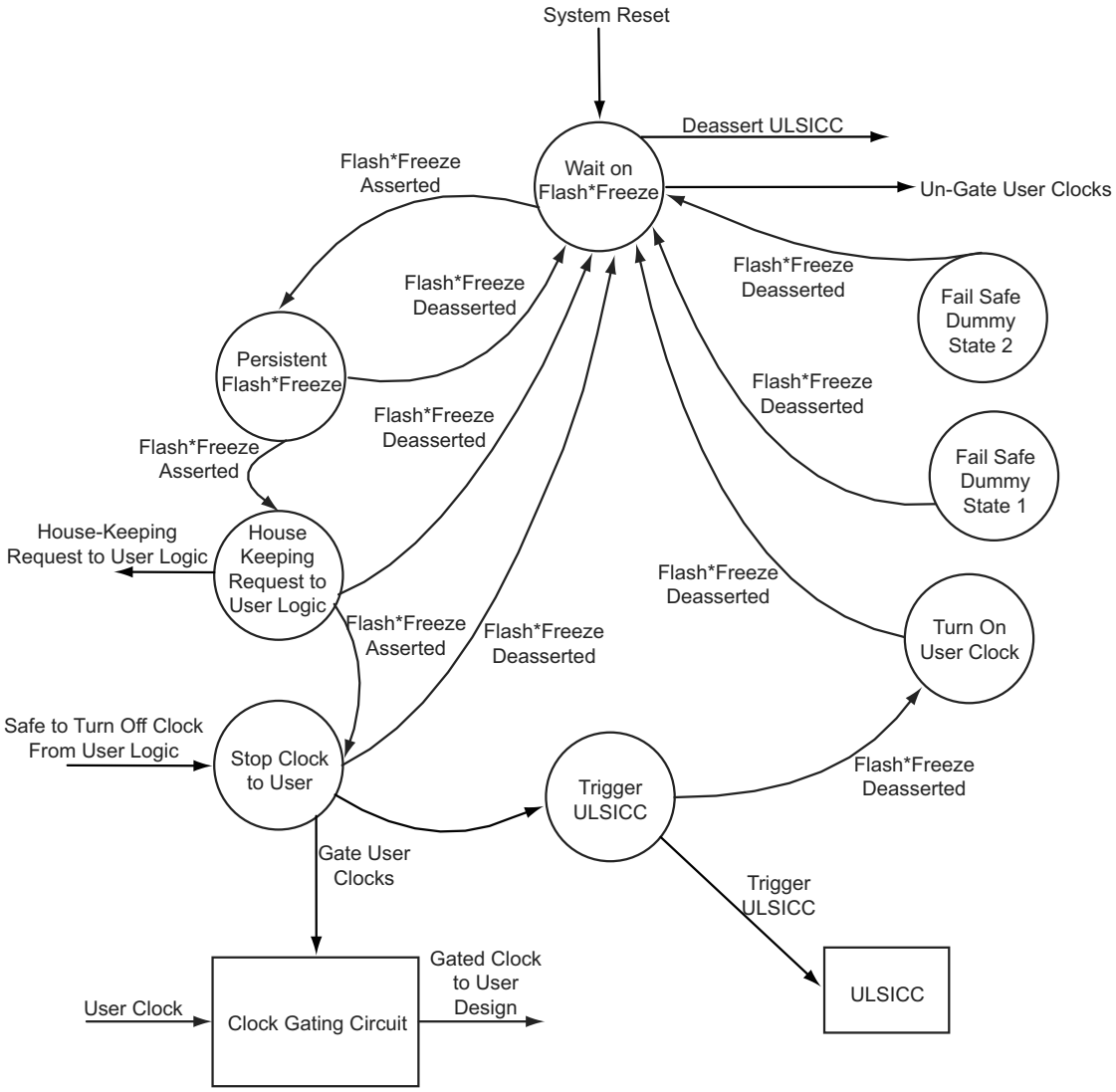


Figure 2-11 • **FSM State Diagram**

Chip and Quadrant Global I/Os

The following sections give an overview of naming conventions and other related I/O information.

Naming of Global I/Os

In low power flash devices, the global I/Os have access to certain clock conditioning circuitry and have direct access to the global network. Additionally, the global I/Os can be used as regular I/Os, since they have identical capabilities to those of regular I/Os. Due to the comprehensive and flexible nature of the I/Os in low power flash devices, a naming scheme is used to show the details of the I/O. The global I/O uses the generic name Gmn/IOuxwByVz. Note that Gmn refers to a global input pin and IOuxwByVz refers to a regular I/O Pin, as these I/Os can be used as either global or regular I/Os. Refer to the I/O Structures chapter of the user's guide for the device that you are using for more information on this naming convention.

Figure 3-4 represents the global input pins connection. It shows all 54 global pins available to access the 18 global networks in ProASIC3E families.

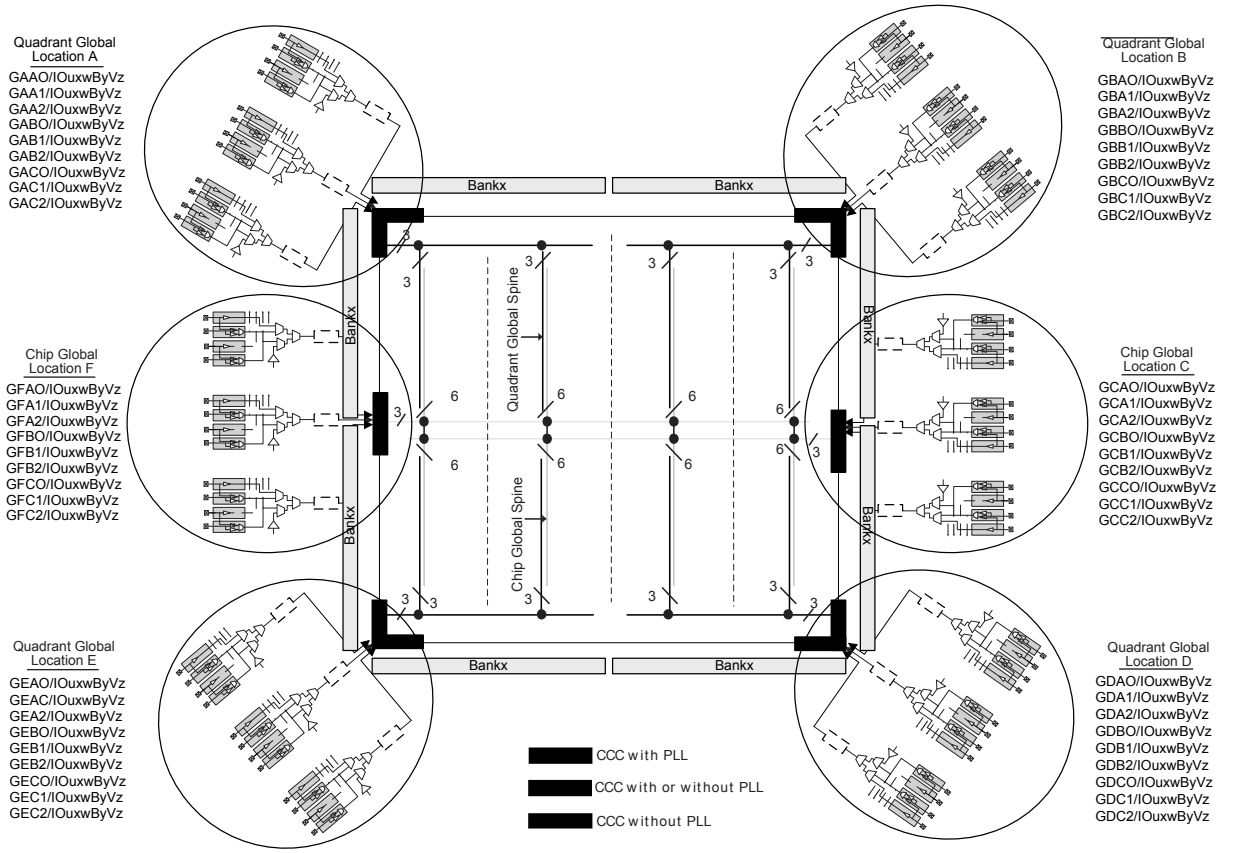


Figure 3-4 • **Global Connections Details**

Spine Architecture

The low power flash device architecture allows the VersaNet global networks to be segmented. Each of these networks contains spines (the vertical branches of the global network tree) and ribs that can reach all the VersaTiles inside its region. The nine spines available in a vertical column reside in global networks with two separate regions of scope: the quadrant global network, which has three spines, and the chip (main) global network, which has six spines. Note that the number of quadrant globals and globals/spines per tree varies depending on the specific device. Refer to Table 3-4 for the clocking resources available for each device. The spines are the vertical branches of the global network tree, shown in Figure 3-3 on page 50. Each spine in a vertical column of a chip (main) global network is further divided into two spine segments of equal lengths: one in the top and one in the bottom half of the die (except in 10 k through 30 k gate devices).

Top and bottom spine segments radiating from the center of a device have the same height. However, just as in the ProASIC^{PLUS}® family, signals assigned only to the top and bottom spine cannot access the middle two rows of the die. The spines for quadrant clock networks do not cross the middle of the die and cannot access the middle two rows of the architecture.

Each spine and its associated ribs cover a certain area of the device (the "scope" of the spine; see Figure 3-3 on page 50). Each spine is accessed by the dedicated global network MUX tree architecture, which defines how a particular spine is driven—either by the signal on the global network from a CCC, for example, or by another net defined by the user. Details of the chip (main) global network spine-selection MUX are presented in Figure 3-8 on page 60. The spine drivers for each spine are located in the middle of the die.

Quadrant spines can be driven from user I/Os or an internal signal from the north and south sides of the die. The ability to drive spines in the quadrant global networks can have a significant effect on system performance for high-fanout inputs to a design. Access to the top quadrant spine regions is from the top of the die, and access to the bottom quadrant spine regions is from the bottom of the die. The A3PE3000 device has 28 clock trees and each tree has nine spines; this flexible global network architecture enables users to map up to 252 different internal/external clocks in an A3PE3000 device.

***Table 3-4* • Globals/Spines/Rows for IGLOO and ProASIC3 Devices**

ProASIC3/ ProASIC3L Devices	IGLOO Devices	Chip Globals	Quadrant Globals (4×3)	Clock Trees	Globals/ Spines per Tree	Total Spines per Device	VersaTiles in Each Tree	Total VersaTiles	Rows in Each Spine
A3PN010	AGLN010	4	0	1	0	0	260	260	4
A3PN015	AGLN015	4	0	1	0	0	384	384	6
A3PN020	AGLN020	4	0	1	0	0	520	520	6
A3PN060	AGLN060	6	12	4	9	36	384	1,536	12
A3PN125	AGLN125	6	12	8	9	72	384	3,072	12
A3PN250	AGLN250	6	12	8	9	72	768	6,144	24
A3P015	AGL015	6	0	1	9	9	384	384	12
A3P030	AGL030	6	0	2	9	18	384	768	12
A3P060	AGL060	6	12	4	9	36	384	1,536	12
A3P125	AGL125	6	12	8	9	72	384	3,072	12
A3P250/L	AGL250	6	12	8	9	72	768	6,144	24
A3P400	AGL400	6	12	12	9	108	768	9,216	24
A3P600/L	AGL600	6	12	12	9	108	1,152	13,824	36
A3P1000/L	AGL1000	6	12	16	9	144	1,536	24,576	48
A3PE600/L	AGLE600	6	12	12	9	108	1,120	13,440	35
A3PE1500		6	12	20	9	180	1,888	37,760	59
A3PE3000/L	AGLE3000	6	12	28	9	252	2,656	74,368	83

External I/O or Local signal as Clock Source

External I/O refers to regular I/O pins are labeled with the I/O convention IOuxwByVz. You can allow the external I/O or internal signal to access the global. To allow the external I/O or internal signal to access the global network, you need to instantiate the CLKINT macro. Refer to Figure 3-4 on page 51 for an example illustration of the connections. Instead of using CLKINT, you can also use PDC to promote signals from external I/O or internal signal to the global network. However, it may cause layout issues because of synthesis logic replication. Refer to the "Global Promotion and Demotion Using PDC" section on page 67 for details.

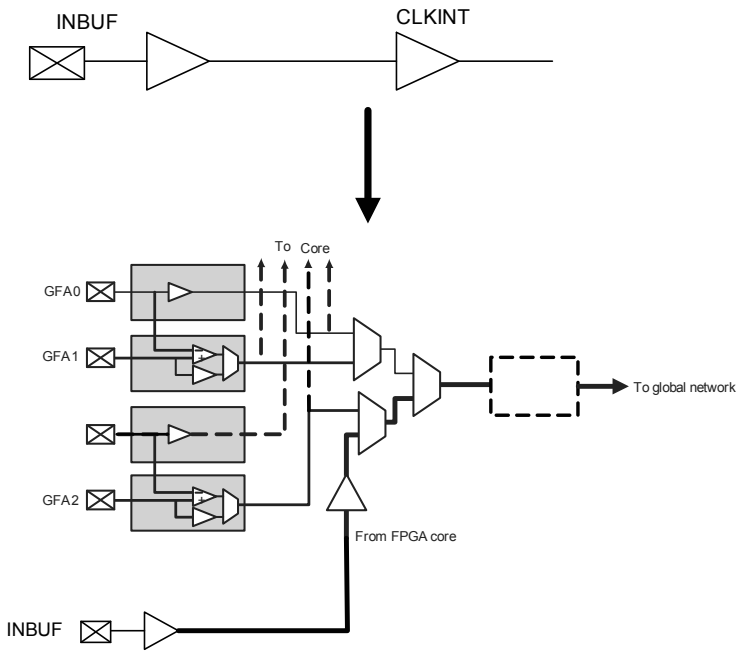


Figure 3-14 • **CLKINT Macro**

Using Global Macros in Synplicity

The Synplify® synthesis tool automatically inserts global buffers for nets with high fanout during synthesis. By default, Synplicity® puts six global macros (CLKBUF or CLKINT) in the netlist, including any global instantiation or PLL macro. Synplify always honors your global macro instantiation. If you have a PLL (only primary output is used) in the design, Synplify adds five more global buffers in the netlist. Synplify uses the following global counting rule to add global macros in the netlist:

1. CLKBUF: 1 global buffer
2. CLKINT: 1 global buffer
3. CLKDLY: 1 global buffer
4. PLL: 1 to 3 global buffers
   – GLA, GLB, GLC, YB, and YC are counted as 1 buffer.
   – GLB or YB is used or both are counted as 1 buffer.
   – GLC or YC is used or both are counted as 1 buffer.

Dynamic PLL Configuration

To generate a dynamically reconfigurable CCC, the user should select **Dynamic CCC** in the configuration section of the SmartGen GUI (Figure 4-26). This will generate both the CCC core and the configuration shift register / control bit MUX.

***Figure 4-26* • SmartGen GUI**

Even if dynamic configuration is selected in SmartGen, the user must still specify the static configuration data for the CCC (Figure 4-27). The specified static configuration is used whenever the MODE signal is set to LOW and the CCC is required to function in the static mode. The static configuration data can be used as the default behavior of the CCC where required.

***Figure 4-27* • Dynamic CCC Configuration in SmartGen**

Recommended Board-Level Considerations

The power to the PLL core is supplied by VCCPLA/B/C/D/E/F (VCCPLx), and the associated ground connections are supplied by VCOMPLA/B/C/D/E/F (VCOMPLx). When the PLLs are not used, the Designer place-and-route tool automatically disables the unused PLLs to lower power consumption. The user should tie unused VCCPLx and VCOMPLx pins to ground. Optionally, the PLL can be turned on/off during normal device operation via the POWERDOWN port (see Table 4-3 on page 84).

PLL Power Supply Decoupling Scheme

The PLL core is designed to tolerate noise levels on the PLL power supply as specified in the datasheets. When operated within the noise limits, the PLL will meet the output peak-to-peak jitter specifications specified in the datasheets. User applications should always ensure the PLL power supply is powered from a noise-free or low-noise power source.

However, in situations where the PLL power supply noise level is higher than the tolerable limits, various decoupling schemes can be designed to suppress noise to the PLL power supply. An example is provided in Figure 4-38. The VCCPLx and VCOMPLx pins correspond to the PLL analog power supply and ground.

Microsemi strongly recommends that two ceramic capacitors (10 nF in parallel with 100 nF) be placed close to the power pins (less than 1 inch away). A third generic 10 µF electrolytic capacitor is recommended for low-frequency noise and should be placed farther away due to its large physical size. Microsemi recommends that a 6.8 µH inductor be placed between the supply source and the capacitors to filter out any low-/medium- and high-frequency noise. In addition, the PCB layers should be controlled so the VCCPLx and VCOMPLx planes have the minimum separation possible, thus generating a good-quality RF capacitor.

For more recommendations, refer to the *Board-Level Considerations* application note.

Recommended 100 nF capacitor:

- Producer BC Components, type X7R, 100 nF, 16 V
- BC Components part number: 0603B104K160BT
- Digi-Key part number: BC1254CT-ND
- Digi-Key part number: BC1254TR-ND

Recommended 10 nF capacitor:

- Surface-mount ceramic capacitor
- Producer BC Components, type X7R, 10 nF, 50 V
- BC Components part number: 0603B103K500BT
- Digi-Key part number: BC1252CT-ND
- Digi-Key part number: BC1252TR-ND

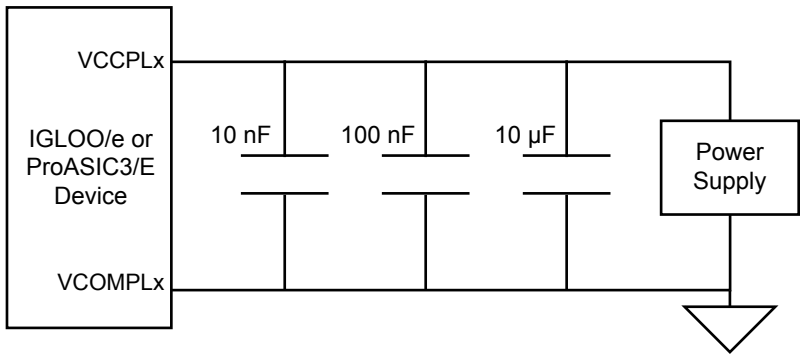
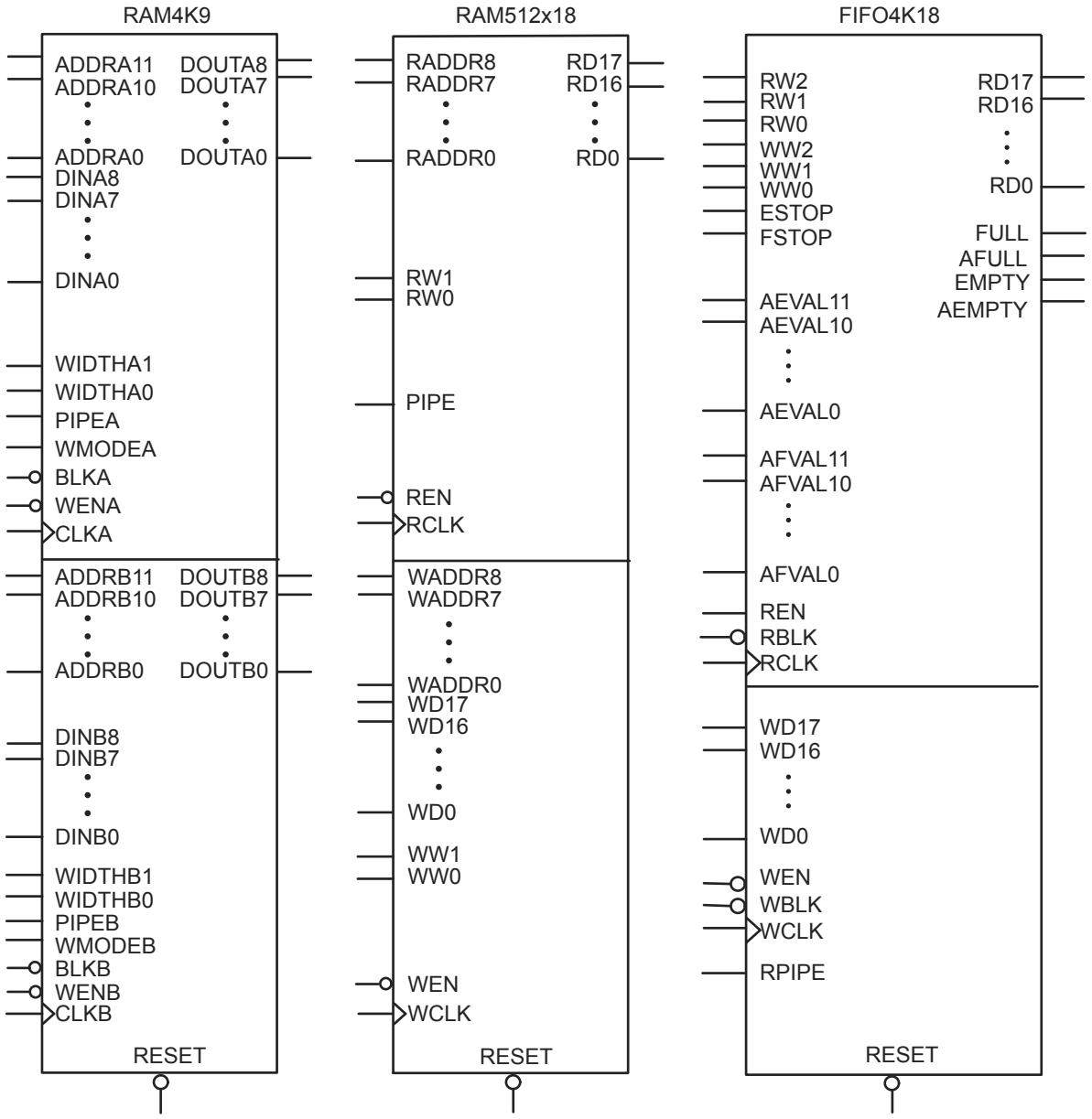


***Figure 4-38* • Decoupling Scheme for One PLL (should be replicated for each PLL used)**



Notes:

1. *Automotive ProASIC3 devices restrict RAM4K9 to a single port or to dual ports with the same clock 180° out of phase (inverted) between clock pins. In single-port mode, inputs to port B should be tied to ground to prevent errors during compile. This warning applies only to automotive ProASIC3 parts of certain revisions and earlier. Contact Technical Support at soc_tech@microsemi.com for information on the revision number for a particular lot and date code.*
2. *For FIFO4K18, the same clock 180° out of phase (inverted) between clock pins should be used.*

***Figure 6-3* • Supported Basic RAM Macros**

Software Support

The SmartGen core generator is the easiest way to select and configure the memory blocks (Figure 6-12). SmartGen automatically selects the proper memory block type and aspect ratio, and cascades the memory blocks based on the user's selection. SmartGen also configures any additional signals that may require tie-off.

SmartGen will attempt to use the minimum number of blocks required to implement the desired memory. When cascading, SmartGen will configure the memory for width before configuring for depth. For example, if the user requests a 256×8 FIFO, SmartGen will use a 512×9 FIFO configuration, not 256×18.

***Figure 6-12* • SmartGen Core Generator Interface**

***Table 7-10* • Hot-Swap Level 3**

Description	Hot-swap while bus idle
Power Applied to Device	Yes
Bus State	Held idle (no ongoing I/O processes during insertion/removal)
Card Ground Connection	Reset must be maintained for 1 ms before, during, and after insertion/removal.
Device Circuitry Connected to Bus Pins	Must remain glitch-free during power-up or power-down
Example Application	Board bus shared with card bus is "frozen," and there is no toggling activity on the bus. It is critical that the logic states set on the bus signal not be disturbed during card insertion/removal.
Compliance of IGLOO and ProASIC3 Devices	30K gate devices, all IGLOOe/ProASIC3E devices: Compliant with two levels of staging (first: GND; second: all other pins) Other IGLOO/ProASIC3 devices: Compliant: Option A – Two levels of staging (first: GND; second: all other pins) together with bus switch on the I/Os Option B – Three levels of staging (first: GND; second: supplies; third: all other pins)

***Table 7-11* • Hot-Swap Level 4**

Description	Hot-swap on an active bus
Power Applied to Device	Yes
Bus State	Bus may have active I/O processes ongoing, but device being inserted or removed must be idle.
Card Ground Connection	Reset must be maintained for 1 ms before, during, and after insertion/removal.
Device Circuitry Connected to Bus Pins	Must remain glitch-free during power-up or power-down
Example Application	There is activity on the system bus, and it is critical that the logic states set on the bus signal not be disturbed during card insertion/removal.
Compliance of IGLOO and ProASIC3 Devices	30K gate devices, all IGLOOe/ProASIC3E devices: Compliant with two levels of staging (first: GND; second: all other pins) Other IGLOO/ProASIC3 devices: Compliant: Option A – Two levels of staging (first: GND; second: all other pins) together with bus switch on the I/Os Option B – Three levels of staging (first: GND; second: supplies; third: all other pins)

IGLOO and ProASIC3

For boards and cards with three levels of staging, card power supplies must have time to reach their final values before the I/Os are connected. Pay attention to the sizing of power supply decoupling capacitors on the card to ensure that the power supplies are not overloaded with capacitance.

Cards with three levels of staging should have the following sequence:

- Grounds
- Powers
- I/Os and other pins

For Level 3 and Level 4 compliance with the 30K gate device, cards with two levels of staging should have the following sequence:

- Grounds
- Powers, I/Os, and other pins

Cold-Sparing Support

Cold-sparing refers to the ability of a device to leave system data undisturbed when the system is powered up, while the component itself is powered down, or when power supplies are floating.

The resistor value is calculated based on the decoupling capacitance on a given power supply. The RC constant should be greater than 3 µs.

To remove resistor current during operation, it is suggested that the resistor be disconnected (e.g., with an NMOS switch) from the power supply after the supply has reached its final value. Refer to the "Power-Up/-Down Behavior of Low Power Flash Devices" section on page 373 for details on cold-sparing.

Cold-sparing means that a subsystem with no power applied (usually a circuit board) is electrically connected to the system that is in operation. This means that all input buffers of the subsystem must present very high input impedance with no power applied so as not to disturb the operating portion of the system.

The 30 k gate devices fully support cold-sparing, since the I/O clamp diode is always off (see Table 7-12 on page 193). If the 30 k gate device is used in applications requiring cold-sparing, a discharge path from the power supply to ground should be provided. This can be done with a discharge resistor or a switched resistor. This is necessary because the 30K gate devices do not have built-in I/O clamp diodes.

For other IGLOO and ProASIC3 devices, since the I/O clamp diode is always active, cold-sparing can be accomplished either by employing a bus switch to isolate the device I/Os from the rest of the system or by driving each I/O pin to 0 V. If the resistor is chosen, the resistor value must be calculated based on decoupling capacitance on a given power supply on the board (this decoupling capacitance is in parallel with the resistor). The RC time constant should ensure full discharge of supplies before cold-sparing functionality is required. The resistor is necessary to ensure that the power pins are discharged to ground every time there is an interruption of power to the device.

IGLOOe and ProASIC3E devices support cold-sparing for all I/O configurations. Standards, such as PCI, that require I/O clamp diodes can also achieve cold-sparing compliance, since clamp diodes get disconnected internally when the supplies are at 0 V.

When targeting low power applications, I/O cold-sparing may add additional current if a pin is configured with either a pull-up or pull-down resistor and driven in the opposite direction. A small static current is induced on each I/O pin when the pin is driven to a voltage opposite to the weak pull resistor. The current is equal to the voltage drop across the input pin divided by the pull resistor. Refer to the "Detailed I/O DC Characteristics" section of the appropriate family datasheet for the specific pull resistor value for the corresponding I/O standard.

For example, assuming an LVTTL 3.3 V input pin is configured with a weak pull-up resistor, a current will flow through the pull-up resistor if the input pin is driven LOW. For LVTTL 3.3 V, the pull-up resistor is ~45 kΩ, and the resulting current is equal to 3.3 V / 45 kΩ = 73 µA for the I/O pin. This is true also when a weak pull-down is chosen and the input pin is driven HIGH. This current can be avoided by driving the input LOW when a weak pull-down resistor is used and driving it HIGH when a weak pull-up resistor is used.

This current draw can occur in the following cases:

User I/O Naming Convention

IGLOO and ProASIC3

Due to the comprehensive and flexible nature of IGLOO and ProASIC3 device user I/Os, a naming scheme is used to show the details of each I/O (Figure 7-19 on page 207 and Figure 7-20 on page 207). The name identifies to which I/O bank it belongs, as well as pairing and pin polarity for differential I/Os.

I/O Nomenclature = FF/Gmn/IOuxwBy

Gmn is only used for I/Os that also have CCC access—i.e., global pins.

FF = Indicates the I/O dedicated for the Flash*Freeze mode activation pin in IGLOO and ProASIC3L devices only

G = Global

m = Global pin location associated with each CCC on the device: A (northwest corner), B (northeast corner), C (east middle), D (southeast corner), E (southwest corner), and F (west middle)

n = Global input MUX and pin number of the associated Global location m—either A0, A1, A2, B0, B1, B2, C0, C1, or C2. Refer to the "Global Resources in Low Power Flash Devices" section on page 47 for information about the three input pins per clock source MUX at CCC location m.

u = I/O pair number in the bank, starting at 00 from the northwest I/O bank and proceeding in a clockwise direction

x = P or U (Positive), N or V (Negative) for differential pairs, or R (Regular—single-ended) for the I/Os that support single-ended and voltage-referenced I/O standards only. U (Positive) or V (Negative)—for LVDS, DDR LVDS, B-LVDS, and M-LVDS only—restricts the I/O differential pair from being selected as an LVPECL pair.

w = D (Differential Pair), P (Pair), or S (Single-Ended). D (Differential Pair) if both members of the pair are bonded out to adjacent pins or are separated only by one GND or NC pin; P (Pair) if both members of the pair are bonded out but do not meet the adjacency requirement; or S (Single-Ended) if the I/O pair is not bonded out. For Differential Pairs (D), adjacency for ball grid packages means only vertical or horizontal. Diagonal adjacency does not meet the requirements for a true differential pair.

B = Bank

y = Bank number (0–3). The Bank number starts at 0 from the northwest I/O bank and proceeds in a clockwise direction.

8 – I/O Structures in IGLOOe and ProASIC3E Devices

Introduction

Low power flash devices feature a flexible I/O structure, supporting a range of mixed voltages (1.2 V, 1.5 V, 1.8 V, 2.5 V, and 3.3 V) through bank-selectable voltages. IGLOO®e, ProASIC®3EL, and ProASIC3E families support Pro I/Os.

Users designing I/O solutions are faced with a number of implementation decisions and configuration choices that can directly impact the efficiency and effectiveness of their final design. The flexible I/O structure, supporting a wide variety of voltages and I/O standards, enables users to meet the growing challenges of their many diverse applications. The Libero SoC software provides an easy way to implement I/O that will result in robust I/O design.

This document first describes the two different I/O types in terms of the standards and features they support. It then explains the individual features and how to implement them in Libero SoC.

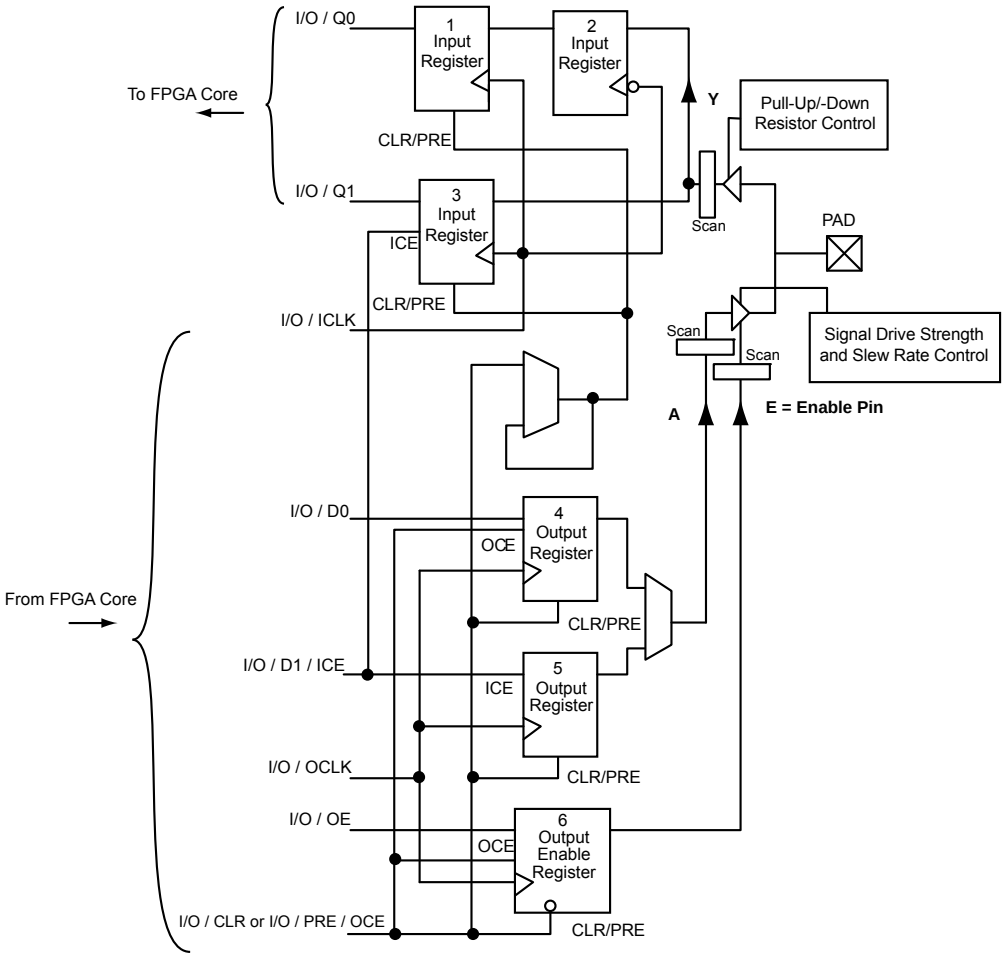


***Figure 8-1* • DDR Configured I/O Block Logical Representation**

IGLOOe and ProASIC3E devices support output slew rate control: high and low. Microsemi recommends the high slew rate option to minimize the propagation delay. This high-speed option may introduce noise into the system if appropriate signal integrity measures are not adopted. Selecting a low slew rate reduces this kind of noise but adds some delays in the system. Low slew rate is recommended when bus transients are expected.

Output Drive

The output buffers of IGLOOe and ProASIC3E devices can provide multiple drive strengths to meet signal integrity requirements. The LVTTL and LVCMOS (except 1.2 V LVCMOS) standards have selectable drive strengths. Other standards have a preset value.

Drive strength should also be selected according to the design requirements and noise immunity of the system.

The output slew rate and multiple drive strength controls are available in LVTTL/LVCMOS 3.3 V, LVCMOS 2.5 V, LVCMOS 2.5 V / 5.0 V input, LVCMOS 1.8 V, and LVCMOS 1.5 V. All other I/O standards have a high output slew rate by default.

For other IGLOOe and ProASIC3E devices, refer to Table 8-15 for more information about the slew rate and drive strength specification.

There will be a difference in timing between the Standard Plus I/O banks and the Advanced I/O banks. Refer to the I/O timing tables in the datasheet for the standards supported by each device.

***Table 8-15* • IGLOOe and ProASIC3E I/O Standards—Output Drive and Slew Rate**

I/O Standards	2 mA	4 mA	6 mA	8 mA	12 mA	16 mA	24 mA	Slew	
LVTTL/LVCMOS 3.3 V	✓	✓	✓	✓	✓	✓	✓	High	Low
LVCMOS 2.5 V	✓	✓	✓	✓	✓	✓	✓	High	Low
LVCMOS 2.5/5.0 V	✓	✓	✓	✓	✓	✓	✓	High	Low
LVCMOS 1.8 V	✓	✓	✓	✓	✓	✓	–	High	Low
LVCMOS 1.5 V	✓	✓	✓	✓	✓	–	–	High	Low

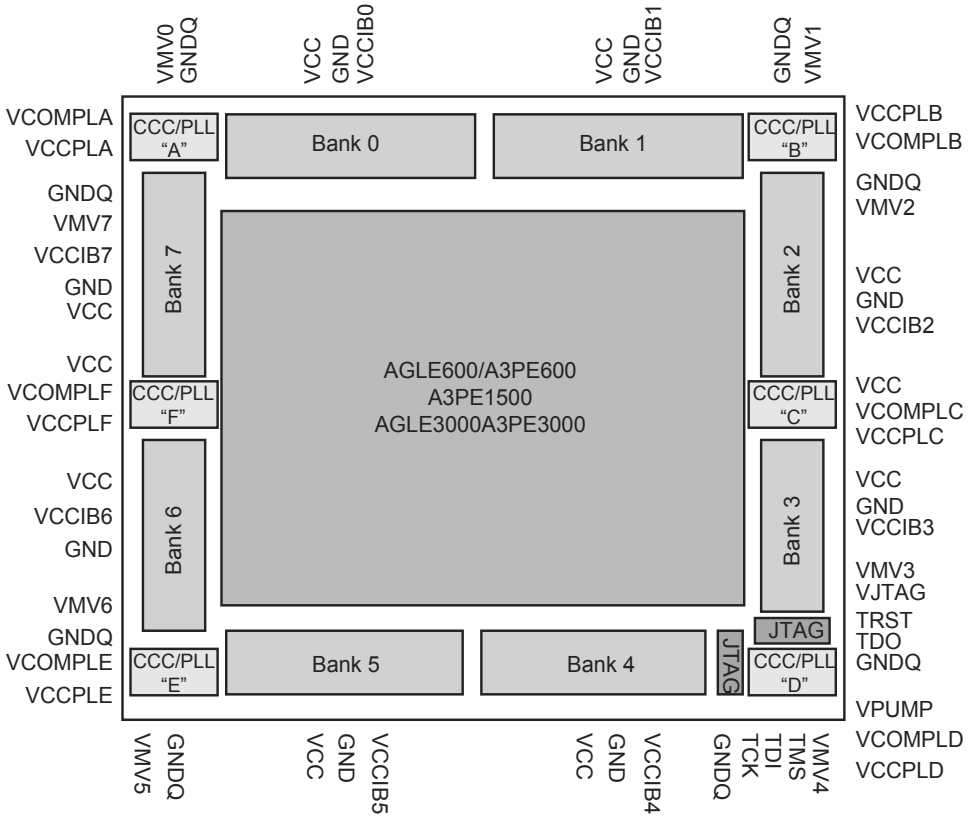


Figure 8-20 • **User I/O Naming Conventions of IGLOOe and ProASIC3E Devices – Top View**

Board-Level Considerations

Low power flash devices have robust I/O features that can help in reducing board-level components. The devices offer single-chip solutions, which makes the board layout simpler and more immune to signal integrity issues. Although, in many cases, these devices resolve board-level issues, special attention should always be given to overall signal integrity. This section covers important board-level considerations to facilitate optimum device performance.

Termination

Proper termination of all signals is essential for good signal quality. Nonterminated signals, especially clock signals, can cause malfunctioning of the device.

For general termination guidelines, refer to the *Board-Level Considerations* application note for Microsemi FPGAs. Also refer to the "Pin Descriptions" chapter of the appropriate datasheet for termination requirements for specific pins.

Low power flash I/Os are equipped with on-chip pull-up/-down resistors. The user can enable these resistors by instantiating them either in the top level of the design (refer to the *IGLOO, Fusion, and ProASIC3 Macro Library Guide* for the available I/O macros with pull-up/-down) or in the I/O Attribute Editor in Designer if generic input or output buffers are instantiated in the top level. Unused I/O pins are configured as inputs with pull-up resistors.

As mentioned earlier, low power flash devices have multiple programmable drive strengths, and the user can eliminate unwanted overshoot and undershoot by adjusting the drive strengths.

Cortex-M1 Device Security

Cortex-M1–enabled devices are shipped with the following security features:

- FPGA array enabled for AES-encrypted programming and verification
- FlashROM enabled for AES-encrypted Write and Verify
- Fusion Embedded Flash Memory enabled for AES-encrypted Write

AES Encryption of Programming Files

Low power flash devices employ AES as part of the security mechanism that prevents invasive and noninvasive attacks. The mechanism entails encrypting the programming file with AES encryption and then passing the programming file through the AES decryption core, which is embedded in the device. The file is decrypted there, and the device is successfully programmed. The AES master key is stored in on-chip nonvolatile memory (flash). The AES master key can be preloaded into parts in a secure programming environment (such as the Microsemi In-House Programming center), and then "blank" parts can be shipped to an untrusted programming or manufacturing center for final personalization with an AES-encrypted bitstream. Late-stage product changes or personalization can be implemented easily and securely by simply sending a STAPL file with AES-encrypted data. Secure remote field updates over public networks (such as the Internet) are possible by sending and programming a STAPL file with AES-encrypted data.

The AES key protects the programming data for file transfer into the device with 128-bit AES encryption. If AES encryption is used, the AES key is stored or preprogrammed into the device. To program, you must use an AES-encrypted file, and the encryption used on the file must match the encryption key already in the device.

The AES key is protected by a FlashLock security Pass Key that is also implemented in each device. The AES key is always protected by the FlashLock Key, and the AES-encrypted file does NOT contain the FlashLock Key. This FlashLock Pass Key technology is exclusive to the Microsemi flash-based device families. FlashLock Pass Key technology can also be implemented without the AES encryption option, providing a choice of different security levels.

In essence, security features can be categorized into the following three options:

- AES encryption with FlashLock Pass Key protection
- FlashLock protection only (no AES encryption)
- No protection

Each of the above options is explained in more detail in the following sections with application examples and software implementation options.

Advanced Encryption Standard

The 128-bit AES standard (FIPS-192) block cipher is the NIST (National Institute of Standards and Technology) replacement for DES (Data Encryption Standard FIPS46-2). AES has been designed to protect sensitive government information well into the 21st century. It replaces the aging DES, which NIST adopted in 1977 as a Federal Information Processing Standard used by federal agencies to protect sensitive, unclassified information. The 128-bit AES standard has 3.4×10^{38} possible 128-bit key variants, and it has been estimated that it would take 1,000 trillion years to crack 128-bit AES cipher text using exhaustive techniques. Keys are stored (securely) in low power flash devices in nonvolatile flash memory. All programming files sent to the device can be authenticated by the part prior to programming to ensure that bad programming data is not loaded into the part that may possibly damage it. All programming verification is performed on-chip, ensuring that the contents of low power flash devices remain secure.

Microsemi has implemented the 128-bit AES (Rijndael) algorithm in low power flash devices. With this key size, there are approximately 3.4×10^{38} possible 128-bit keys. DES has a 56-bit key size, which provides approximately 7.2×10^{16} possible keys. In their AES fact sheet, the National Institute of Standards and Technology uses the following hypothetical example to illustrate the theoretical security provided by AES. If one were to assume that a computing system existed that could recover a DES key in a second, it would take that same machine approximately 149 trillion years to crack a 128-bit AES key. NIST continues to make their point by stating the universe is believed to be less than 20 billion years old.[1]

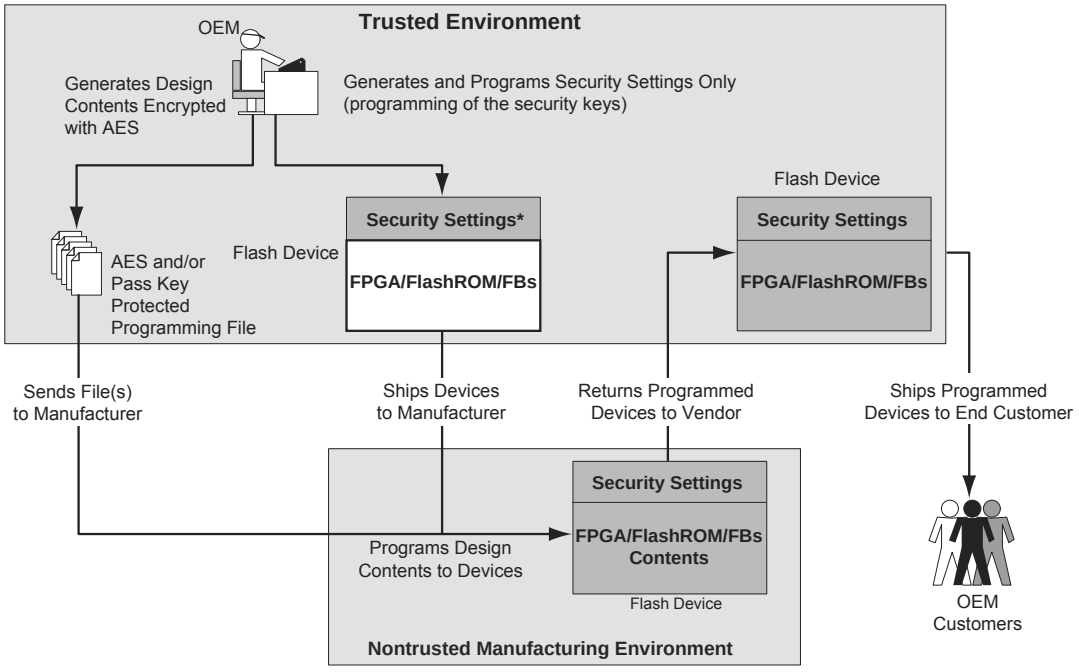
Application 1: Trusted Environment

As illustrated in Figure 12-7, this application allows the programming of devices at design locations where research and development take place. Therefore, encryption is not necessary and is optional to the user. This is often a secure way to protect the design, since the design program files are not sent elsewhere. In situations where production programming is not available at the design location, programming centers (such as Microsemi In-House Programming) provide a way of programming designs at an alternative, secure, and trusted location. In this scenario, the user generates a STAPL programming file from the Designer software in plaintext format, containing information on the entire design or the portion of the design to be programmed. The user can choose to employ the FlashLock Pass Key feature with the design. Once the design is programmed to unprogrammed devices, the design is protected by this FlashLock Pass Key. If no future programming is needed, the user can consider permanently securing the IGLOO and ProASIC3 device, as discussed in the "Permanent FlashLock" section on page 307.

Application 2: Nontrusted Environment—Unsecured Location

Often, programming of devices is not performed in the same location as actual design implementation, to reduce manufacturing cost. Overseas programming centers and contract manufacturers are examples of this scenario.

To achieve security in this case, the AES key and the FlashLock Pass Key can be initially programmed in-house (trusted environment). This is done by generating a programming file with only the security settings and no design contents. The design FPGA core, FlashROM, and (for Fusion) FB contents are generated in a separate programming file. This programming file must be set with the same AES key that was used to program to the device previously so the device will correctly decrypt this encrypted programming file. As a result, the encrypted design content programming file can be safely sent off-site to nontrusted programming locations for design programming. Figure 12-7 shows a more detailed flow for this application.



Notes:

1. *Programmed portion indicated with dark gray.*
2. *Programming of FBs applies to Fusion only.*

Figure 12-7 • **Application 2: Device Programming in a Nontrusted Environment**

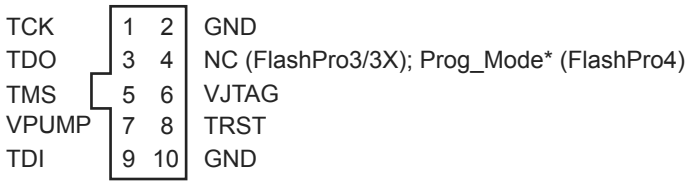
ISP Programming Header Information

The FlashPro4/3/3X programming cable connector can be connected with a 10-pin, 0.1"-pitch programming header. The recommended programming headers are manufactured by AMP (103310-1) and 3M (2510-6002UB). If you have limited board space, you can use a compact programming header manufactured by Samtec (FTSH-105-01-L-D-K). Using this compact programming header, you are required to order an additional header adapter manufactured by Microsemi SoC Products Group (FP3-10PIN-ADAPTER-KIT).

Existing ProASIC^{PLUS} family customers who are using the Samtec Small Programming Header (FTSH-113-01-L-D-K) and are planning to migrate to IGLOO or ProASIC3 devices can also use FP3-10PIN-ADAPTER-KIT.

***Table 13-3* • Programming Header Ordering Codes**

Manufacturer	Part Number	Description
AMP	103310-1	10-pin, 0.1"-pitch cable header (right-angle PCB mount angle)
3M	2510-6002UB	10-pin, 0.1"-pitch cable header (straight PCB mount angle)
Samtec	FTSH-113-01-L-D-K	Small programming header supported by FlashPro and Silicon Sculptor
Samtec	FTSH-105-01-L-D-K	Compact programming header
Samtec	FFSD-05-D-06.00-01-N	10-pin cable with 50 mil pitch sockets; included in FP3-10PIN-ADAPTER-KIT.
Microsemi	FP3-10PIN-ADAPTER-KIT	Transition adapter kit to allow FP3 to be connected to a micro 10-pin header (50 mil pitch). Includes a 6 inch Samtec FFSD-05-D-06.00-01-N cable in the kit. The transition adapter board was previously offered as FP3-26PIN-ADAPTER and includes a 26-pin adapter for design transitions from ProASIC^{PLUS} based boards to ProASIC3 based boards.



*Note: *Prog_Mode on FlashPro4 is an output signal that goes High during device programming and returns to Low when programming is complete. This signal can be used to drive a system to provide a 1.5 V programming signal to IGLOO nano, ProASIC3L, and RT ProASIC3 devices that can run with 1.2 V core voltage but require 1.5 V for programming. IGLOO nano V2 devices can be programmed at 1.2 V core voltage (when using FlashPro4 only), but IGLOO nano V5 devices are programmed with a VCC core voltage of 1.5 V.*

***Figure 13-5* • Programming Header (top view)**

14 – Core Voltage Switching Circuit for IGLOO and ProASIC3L In-System Programming

Introduction

The IGLOO® and ProASIC®3L families offer devices that can be powered by either 1.5 V or, in the case of V2 devices, a core supply voltage anywhere in the range of 1.2 V to 1.5 V, in 50 mV increments.

Since IGLOO and ProASIC3L devices are flash-based, they can be programmed and reprogrammed multiple times in-system using Microsemi FlashPro3. FlashPro3 uses the JTAG standard interface (IEEE 1149.1) and STAPL file (defined in JESD 71 to support programming of programmable devices using IEEE 1149.1) for in-system configuration/programming (IEEE 1532) of a device. Programming can also be executed by other methods, such as an embedded microcontroller that follows the same standards above.

All IGLOO and ProASIC3L devices must be programmed with the VCC core voltage at 1.5 V. Therefore, applications using IGLOO or ProASIC3L devices powered by a 1.2 V supply must switch the core supply to 1.5 V for in-system programming.

The purpose of this document is to describe an easy-to-use and cost-effective solution for switching the core supply voltage from 1.2 V to 1.5 V during in-system programming for IGLOO and ProASIC3L devices.

2. VCC rises to 1.5 V before programming begins.

Figure 14-3 • **Programming Algorithm**

The oscilloscope plot in Figure 14-3 shows a wider time interval for the programming algorithm and includes the TDI and TMS signals from the FlashPro3. These signals carry the programming information that is programmed into the device and should only start toggling after the V_{CC} core voltage reaches 1.5 V. Again, TRST from FlashPro3 and the V_{CC} core voltage of the IGLOO device are labeled. As shown in Figure 14-3, TDI and TMS are floating initially, and the core voltage is 1.2 V. When a programming command on the FlashPro3 is executed, TRST is driven HIGH and TDI is momentarily driven to ground. In response to the HIGH TRST signal, the circuit responds and pulls the core voltage to 1.5 V. After 100 ms, TRST is briefly driven LOW by the FlashPro software. This is expected behavior that ensures the device JTAG state machine is in Reset prior to programming. TRST remains HIGH for the duration of the programming. It can be seen in Figure 14-3 that the VCC core voltage signal remains at 1.5 V for approximately 50 ms before information starts passing through on TDI and TMS. This confirms that the voltage switching circuit drives the VCC core supply voltage to 1.5 V prior to programming.

Related Documents

Datasheets

ProASIC3 Flash Family FPGAs

http://www.microsemi.com/soc/documents/PA3_DS.pdf

ProASIC3E Flash Family FPGAs

http://www.microsemi.com/soc/documents/PA3E_DS.pdf

List of Changes

The following table lists critical changes that were made in each revision of the chapter.

Date	Changes	Page
v1.2 (December 2008)	IGLOO nano and ProASIC3 nano devices were added to the document as supported device types.	
v1.1 (October 2008)	The "Introduction" section was updated to add Military ProASIC3EL and RT ProASIC3 devices to the list of devices that can have inputs driven in while the device is not powered.	373
	The "Flash Devices Support Power-Up Behavior" section was revised to include new families and make the information more concise.	374
	The "Cold-Sparing" section was revised to add Military ProASIC3/EL and RT ProASIC3 devices to the lists of devices with and without cold-sparing support.	382
	The "Hot-Swapping" section was revised to add Military ProASIC3/EL and RT ProASIC3 devices to the lists of devices with and without hot-swap support. AGL400 was added to the list of devices that do not support hot-swapping.	383
v1.0 (August 2008)	This document was revised, renamed, and assigned a new part number. It now includes data for the IGLOO and ProASIC3L families.	N/A
v1.3 (March 2008)	The "List of Changes" section was updated to include the three different I/O Structure handbook chapters.	384
v1.2 (February 2008)	The first sentence of the "PLL Behavior at Brownout Condition" section was updated to read, "When PLL power supply voltage and/or V_{CC} levels drop below the VCC brownout levels (0.75 V ± 0.25 V), the PLL output lock signal goes low and/or the output clock is lost."	381
v1.1 (January 2008)	The "PLL Behavior at Brownout Condition" section was added.	381